

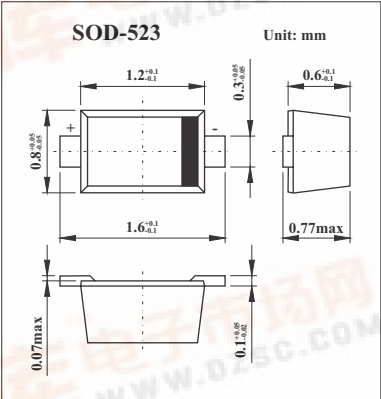
SMD Type

Diodes

Silicon Epitaxial Planar Pin Diode
HVC133

■ Features

- Low capacitance.(C=1.0pF max)
- Low forward resistance. (rf=0.7 Ω max)



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Reverse voltage	VR	30	V
Power dissipation	Pd	150	mW
Junction temperature	Tj	125	℃
Storage temperature	Tstg	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse voltage	VR	IR = 1 μA	30			V
Reverse current	IR	VR = 25 V			100	nA
Forward voltage		IF = 2 mA			0.85	V
Capacitance	C1	VR = 1 V, f = 1 MHz			1.0	pF
	C6	VR = 6 V, f = 2 MHz			0.9	
Forward resistance	rf	IF = 2 mA, f = 100 MHz		0.55	0.7	Ω

■ Marking

Marking	P3
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